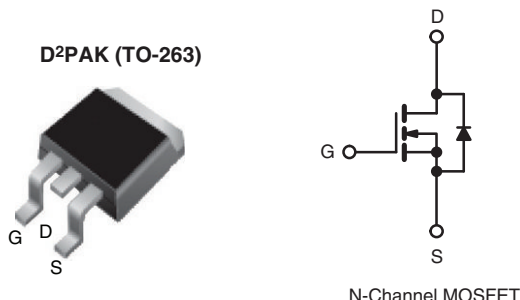


E Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	550	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.145
Q_g (Max.) (nC)	86	
Q_{gs} (nC)	14	
Q_{gd} (nC)	25	
Configuration	Single	



FEATURES

- Low figure-of-merit (FOM): $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Hard switched topologies
- Power factor correction power supplies (PFC)
- Switch mode power supplies (SMPS)
 - PC silver box / ATX power supplies
- Lighting
 - Two stage LED lighting

ORDERING INFORMATION

Package	D2PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHB25N50E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current ^a	I_{DM}	50	
Linear Derating Factor		0.2	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	273	mJ
Maximum Power Dissipation	P_D	250	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	65	V/ns
Reverse Diode dV/dt ^d		25	
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 4.4$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

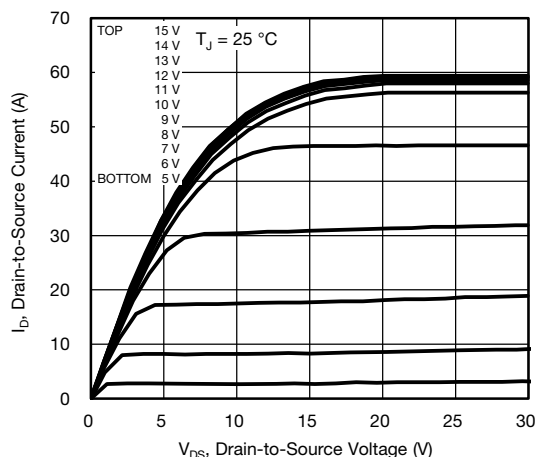
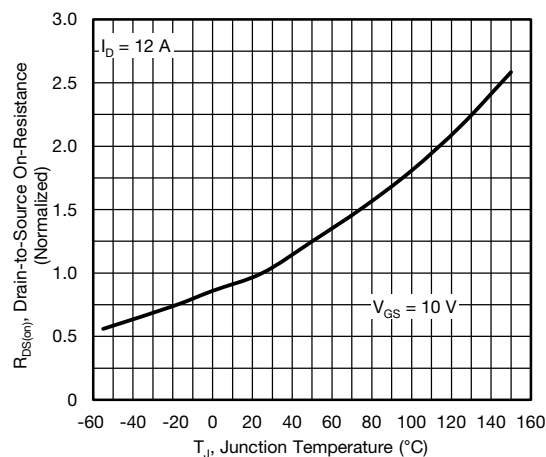
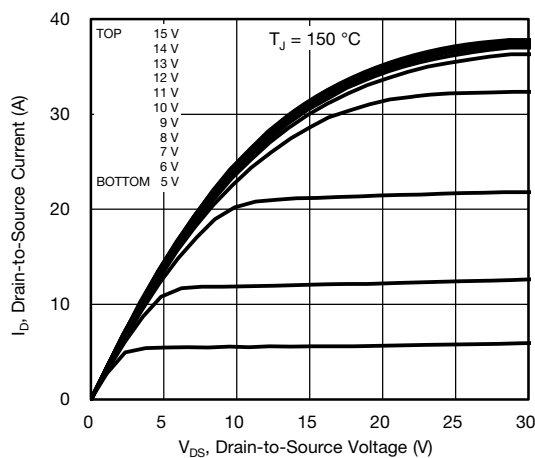
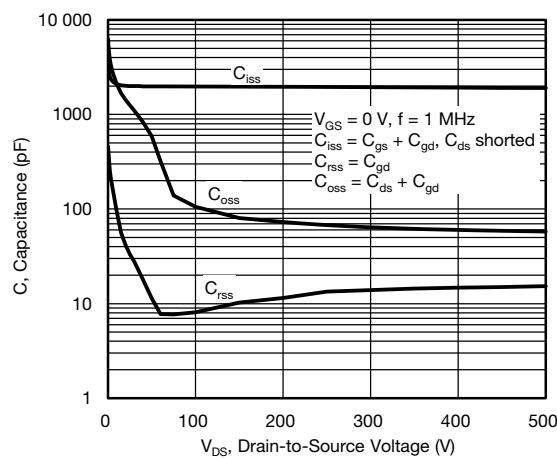
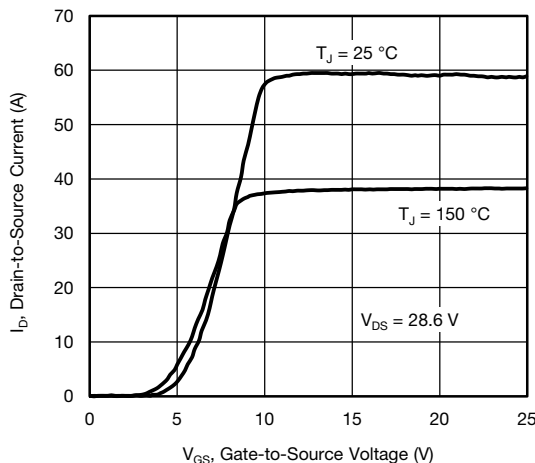
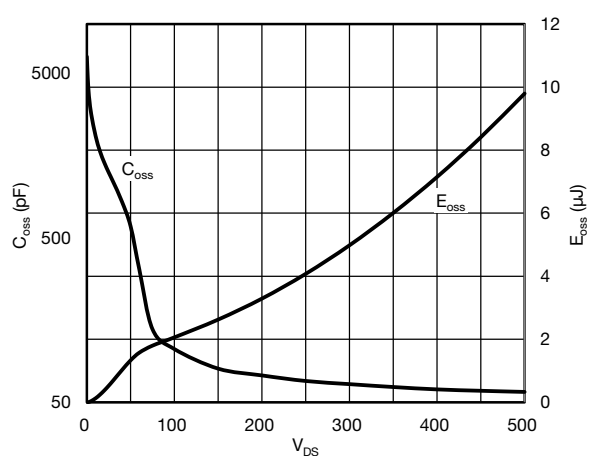
THERMAL RESISTANCE RATINGS

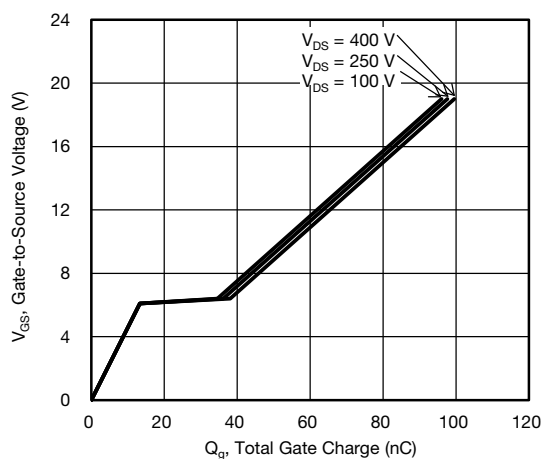
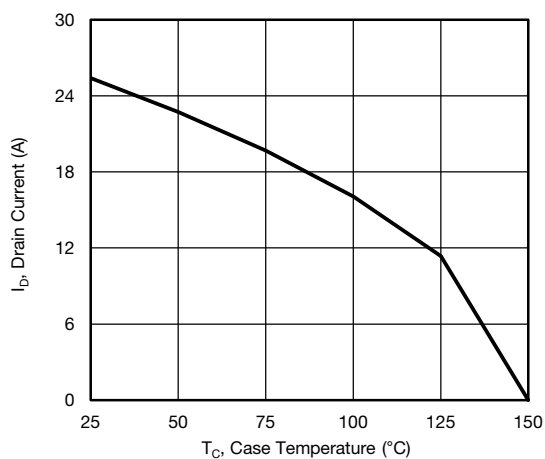
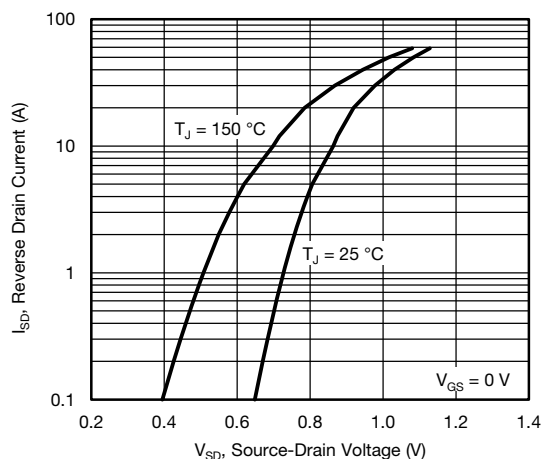
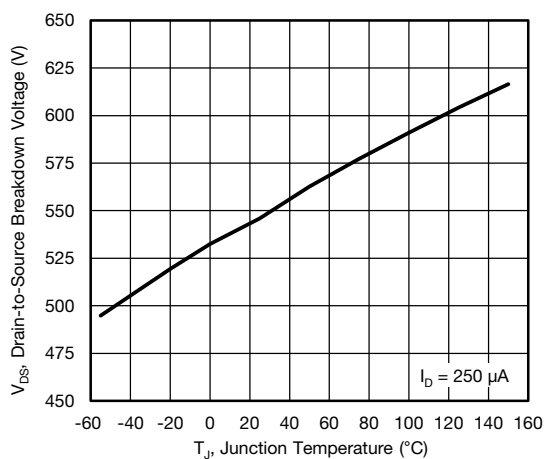
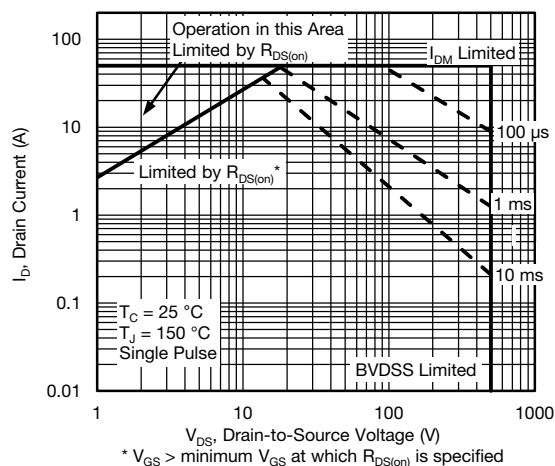
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.5	

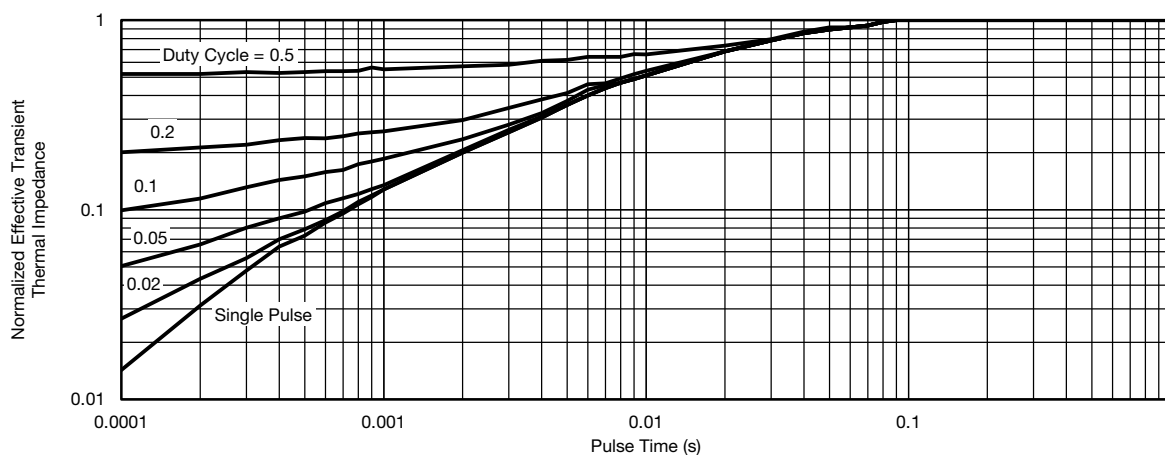
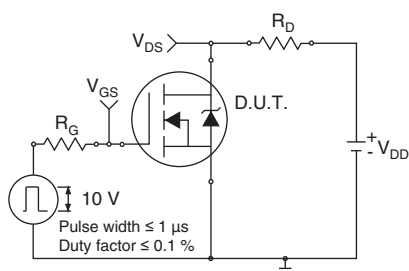
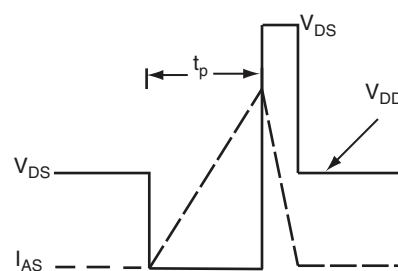
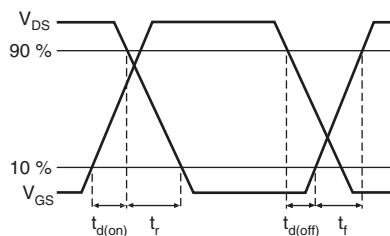
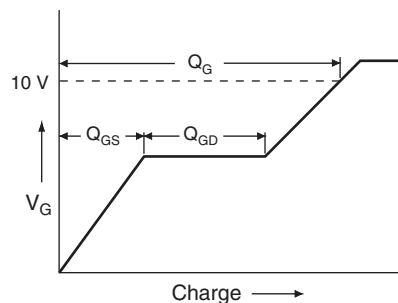
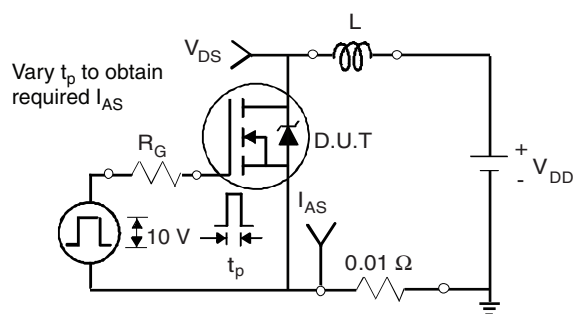
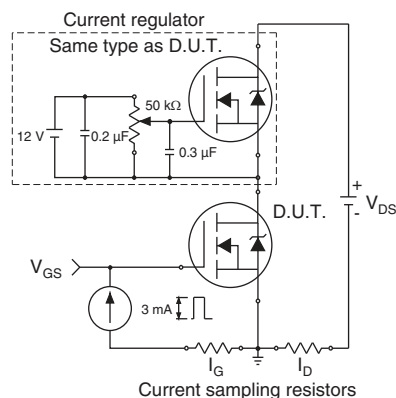
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$	-	0.59	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$	-	-	25	μA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$	-	0.125	0.145	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}$, $I_D = 12\text{ A}$	-	6.6	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$	-	1980	-	pF
Output Capacitance	C_{oss}		-	105	-	
Reverse Transfer Capacitance	C_{rss}		-	8	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 400\text{ V}$, $V_{GS} = 0\text{ V}$	-	105	-	
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$		-	285	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 12\text{ A}$, $V_{DS} = 400\text{ V}$	-	57	86	nC
Gate-Source Charge	Q_{gs}		-	14	-	
Gate-Drain Charge	Q_{gd}		-	25	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 400\text{ V}$, $I_D = 12\text{ A}$ $R_g = 9.1\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	19	38	ns
Rise Time	t_r		-	36	72	
Turn-Off Delay Time	$t_{d(off)}$		-	57	86	
Fall Time	t_f		-	29	58	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	-	0.56	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	12	A
Pulsed Diode Forward Current	I_{SM}		-	-	50	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 16.5\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 25\text{ V}$	-	338	-	ns
Reverse Recovery Charge	Q_{rr}		-	5.3	-	μC
Reverse Recovery Current	I_{RRM}		-	29	-	A

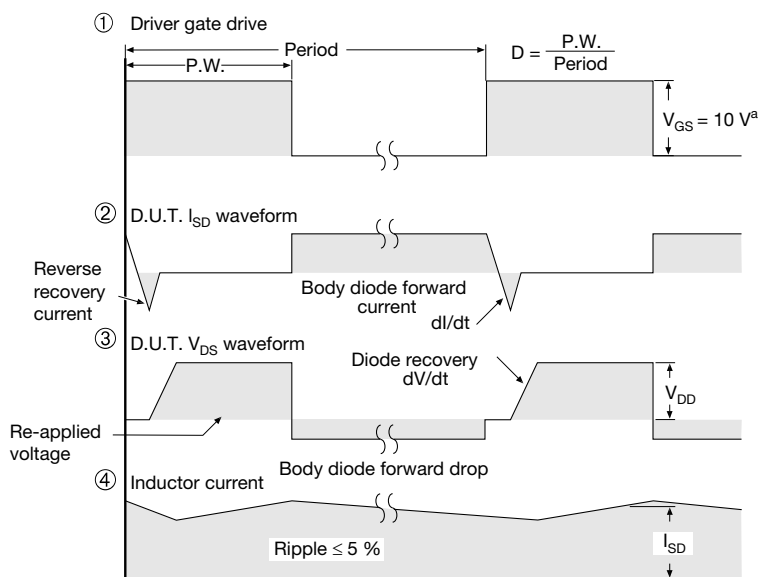
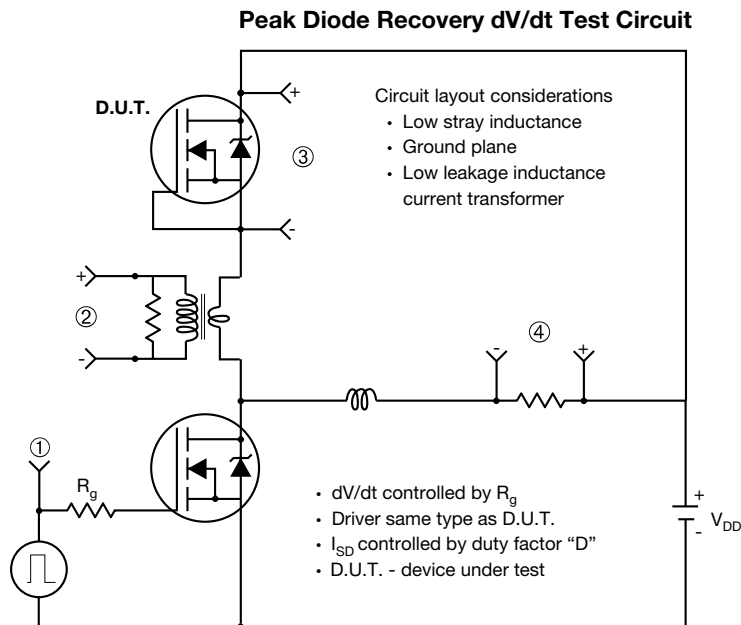
Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_OSS and E_OSS vs. V_DS


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

Fig. 9 - Maximum Safe Operating Area


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit


Note

a. $V_{GS} = 5 V$ for logic level devices

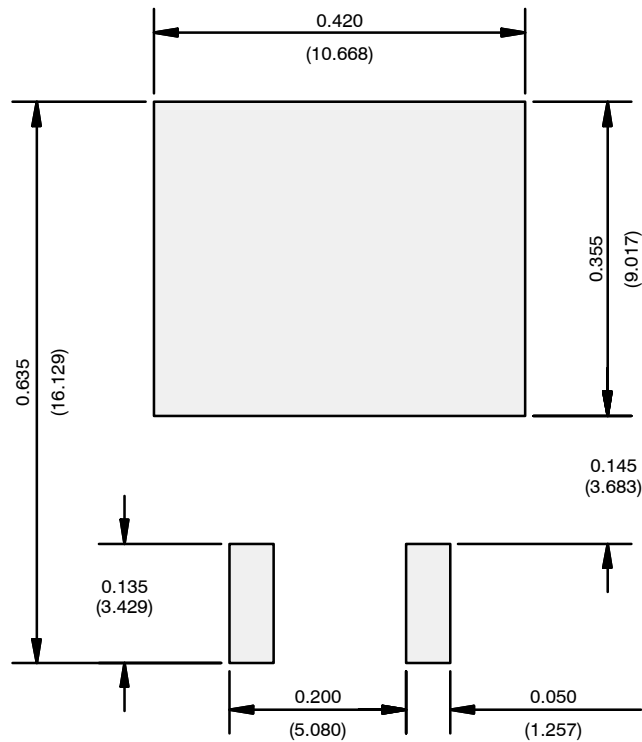
Fig. 19 - For N-Channel

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	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

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RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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